MASWSS0117



GaAs SPDT 2.7 V High Power Switch DC - 3.0 GHz

Rev. V2

Features

Low Voltage Operation: 2.7 V

High IP3: +56 dBm

Low Insertion Loss: 0.30 dB at 1 GHz

High Isolation: 25 dB at 1 GHz

SC70 6-Lead Package

0.5 micron GaAs PHEMT Process

Description

M/A-COM's MASWSS0117 is a GaAs PHEMT MMIC single pole double throw (SPDT) high power switch in a low cost SC70 6-lead package. The MASWSS0117 is ideally suited for applications where high power, low control voltage, low insertion loss, high isolation, small size and low cost are required.

Typical applications are for CDMA handset systems that connect separate transceiver and/or GPS functions to a common antenna, as well as other related handset and general purpose applications. MASWSS0117 can be used in all systems operating up to 3.0 GHz requiring high power at low control voltage.

The MASWSS0117 is fabricated using a 0.5 micron gate length GaAs PHEMT process. The process features full passivation for performance and reliabil-

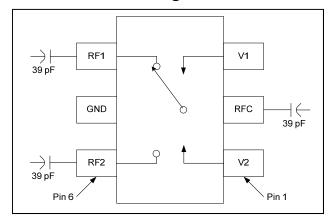
Ordering Information¹

Commitment to produce in volume is not guaranteed.

Part Number	Package
MASWSS0117	Bulk Packaging
MASWSS0117TR	1000 piece reel
MASWSS0117TR-3000	3000 piece reel
MASWSS0117SMB	Sample Test Board

1. Reference Application Note M513 for reel size information.

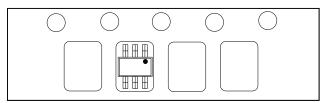
Functional Block Diagram



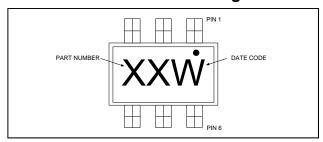
Pin Configuration

Pin No.	Pin Name	Description	
1	V2	Vcontrol 2	
2	RFC	RF Common	
3	V1	Vcontrol 1	
4	RF1	RF Port 1	
5	GND	RF Ground	
6	RF2	RF Port 2	

MASWSS0117 orientation in tape



MASWSS0117 Device Marking



- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298 Visit www.macomtech.com for additional data sheets and product information.

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Electrical Specifications: $T_A = 25^{\circ}C$, $V_C = 0 \text{ V} / 2.7 \text{ V}$, $Z_0 = 50 \Omega^2$

Parameter	Test Conditions	Units	Min.	Тур.	Max.
Insertion Loss ³	DC – 1 GHz 1 – 2 GHz 2 - 3 GHz	dB dB dB	_ _ _	0.30 0.35 0.35	0.65 — —
Isolation	DC – 1 GHz 1 – 2 GHz 2 - 3 GHz	dB dB dB	23 	25 19 15	
Return Loss	DC – 3 GHz	dB	_	20	_
IP3	825 MHz Two Tone, +24 dBm Total Pin, 5 MHz Spacing	dBm	_	56	_
Cross Modulation	For Cell Band: Two-tone signal input: Tx1 = +22 dBm @ 820 MHz, Tx2 = +22 dBm @ 821 MHz, RX interfere = -23 dBm @ 869 MHz.	dBm	_	-99	
	For PCS Band: Two-tone signal input: Tx1 = +18 dBm @ 1880 MHz, Tx2 = +18 dBm @ 1881 MHz, RX interfere = -23 dBm @ 1960 MHz.	dBm	_	-94	1
P0.1dB	1.0 GHz	dBm	_	38	_
Trise, Tfall	10% to 90% RF, 90% to 10% RF	nS	_	70	_
Ton, Toff	50% control to 90% RF 50% control to 10% RF	nS	_	100	_
Transients	In Band	mV	_	25	_
Control Current	V _C = 2.7 V	μΑ	_	5	20

- 2. For positive voltage control, external DC blocking capacitors are required on all RF ports.
- 3. Insertion loss can be optimized by varying the DC blocking capacitor value, e.g. 1000 pF for 100 MHz 1 GHz, 39 pF for 0.5 3 GHz.

Absolute Maximum Ratings ^{4,5}

Parameter	Absolute Maximum	
Input Power (0.5 - 3 GHz, 3 V Control)	+38 dBm	
Operating Voltage	+8.5 volts	
Operating Temperature	-40°C to +85°C	
Storage Temperature	-65°C to +150°C	

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.

Truth Table ^{6,7,8}

V1	V2	ANT-RF1	ANT - RF2
1	0	On	Off
0	1	Off	On

- For positive voltage control, external DC blocking capacitors are required on all RF ports.
- Differential voltage, V (state 1) V (state 0), must be +2.7 V minimum, but must not exceed 8.5 V.
- 8. 0 = -5 V to +2.3 V, 1 = -2.3 V to +5 V.

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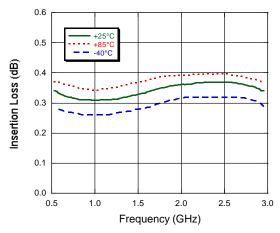


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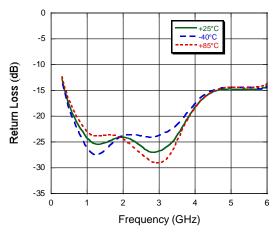
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Typical Performance Curves vs. Frequency, 39 pF

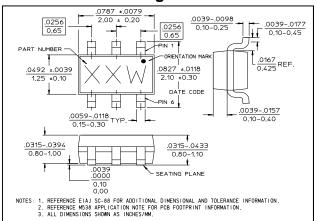
Insertion Loss



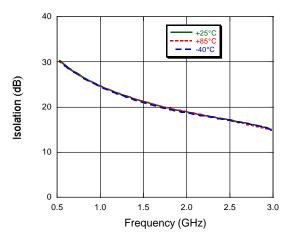
Return Loss



SC-70 Plastic Package[†]



Isolation



Qualification

Qualified to M/A-COM specification REL-201, Process Flow -2.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.